TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2573FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

The TC7MA2573FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the

CMOS low power dissipation. It is also designed with over voltage tolerant inputs and

outputs up to 3.6 V.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}).

When the $\overline{\text{OE}}$ input is high, the eight outputs are in a high impedance state.

The 26 Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

Features

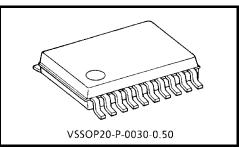
- 26Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: t_{pd} = 5.1 ns (max) (V_{CC} = 3.0~3.6 V) t_{pd} = 6.1 ns (max) (V_{CC} = 2.3~2.7 V)

$$t_{pd} = 9.8 \text{ ns} (\text{max}) (V_{CC} = 1.8 \text{ V})$$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA} \text{ (min)} (V_{CC} = 3.0 \text{ V})$
 - $I_{OH}/I_{OL} = \pm 8 \text{ mA} (\text{min}) (V_{CC} = 2.3 \text{ V})$

 $I_{OH}/I_{OL} = \pm 4 \text{ mA} \text{ (min)} (V_{CC} = 1.8 \text{ V})$

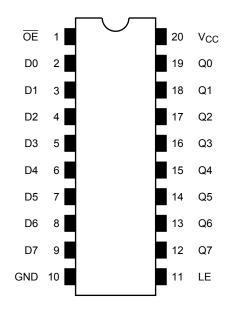
- Latch-up performance: -300 mA
- ESD performance: Machine model $\ge \pm 200 \text{ V}$
 - Human body model $\ge \pm 2000 \text{ V}$
- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.



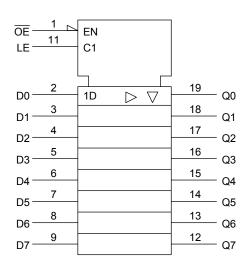
Weight: 0.03 g (typ.)

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Pin Assignment (top view)



IEC Logic Level



Truth Table

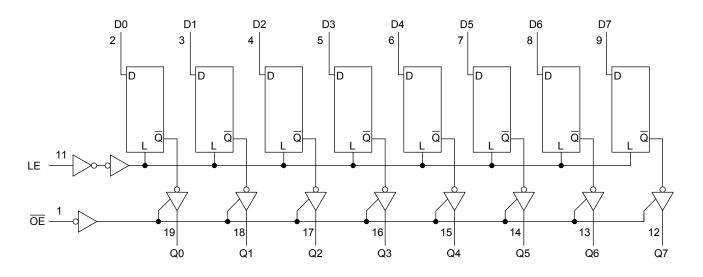
	Inputs					
ŌĒ	LE	D	Outputs			
Н	Х	Х	Z			
L	L	Х	Q _n			
L	Н	L	L			
L	Н	Н	Н			

X: Don't care

Z: High impedance

 $\mathsf{Q}_{\mathsf{n}}:\mathsf{Q}$ outputs are latched at the time when the LE inputs is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note 2)	V	
DC output voltage	Vout	-0.5~V _{CC} + 0.5 (Note 3)	v	
Input diode current	lık	-50	mA	
Output diode current	I _{OK}	±50 (Note 4)	mA	
DC output current	IOUT	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	Vee	1.8~3.6	V
Supply vollage	V _{CC}	1.2~3.6 (Note 2)	v
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	Varia	0~3.6 (Note 3)	V
Output voltage	Vout	0~V _{CC} (Note 4)	v
		±12 (Note 5)	
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

- Note 3: Off-state
- Note 4: High or low state

Note 5: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 V$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = –40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics S		Symbol	I Test Condition			Min	n Max	Unit
		Symbol	Tes	Condition	V _{CC} (V)	IVIIII	IVIAX	Unit
Input voltage	High level	VIH		—	2.7~3.6	2.0	_	V
input voltage	Low level	VIL		—	2.7~3.6	_	0.8	v
				I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_	
	High level	VOH	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OH} = -6 mA	2.7	2.2	_	
	-			I _{OH} = -8 mA	3.0	2.4	_	
Output voltage				I _{OH} = -12 mA	3.0	2.2	_	V
			$I_{OL} = 100 \ \mu A$	2.7~3.6	_	0.2		
	Low level	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 6 \text{ mA}$	2.7	_	0.4	
	Low level			I _{OL} = 8 mA	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input leakage curre	ent	l _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μA
	1-1		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$			10.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V	V _{OUT} = 0~3.6 V		_	±10.0	μA
Power off leakage	current	IOFF	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μA
		Icc	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply of	Quiescent supply current		$V_{CC} \leqq (V_{IN}, V_{OUT}) \leqq$	3.6 V	2.7~3.6	_	±20.0	μA
		Δlcc	$V_{IH} = V_{CC} - 0.6 V$ (pe	er input)	2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	istics	Symbol	Test	Test Condition		Min	Max	Unit		
Input voltago	High level	VIH		_	2.3~2.7	1.6	_	V		
Input voltage	Low level	VIL		_	2.3~2.7	_	0.7	v		
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_			
	High level	VOH	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_			
Output voltage			$I_{OH} = -6 \text{ mA}$	2.3	1.8	_	v			
			I _{OH} = -8 mA	2.3	1.7	—				
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \ \mu A$	2.3~2.7	_	0.2			
	Low level	V _{OL}		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 6 \text{ mA}$	2.3	_	0.4	
				$I_{OL} = 8 \text{ mA}$	2.3	_	0.6			
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μA		
2 state output off a	tata aurrant	1	$V_{IN} = V_{IH} \text{ or } V_{IL}$		2.3~2.7	_	±10.0	A		
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μA		
Power off leakage	current	IOFF	$V_{IN}, V_{OUT} = 0 \sim 3.6 \text{ V}$		0	—	10.0	μA		
Quiescent supply of			$V_{IN} = V_{CC}$ or GND		2.3~2.7	_	20.0	μA		
Quiescent supply (unent	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3$	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		—	±20.0	μА		

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit				
Input voltage	High level	VIH		_	1.8~2.3	$0.7 \times V_{CC}$	_	V				
input voltage	Low level	VIL		_	1.8~2.3		$0.2 \times V_{CC}$	v				
	High level	Vон	VIN = VIH or VIL	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_					
Output voltage				I _{OH} = -4 mA	1.8	1.4	_	V				
	Low level			I _{OL} = 100 μA	1.8	_	0.2					
	LOW IEVEI	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 4 \text{ mA}$	1.8	_	0.3					
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μA				
3-state output off-sta	ate current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8		±10.0	μA				
Power off leakage c	urrent	IOFF	$V_{IN}, V_{OUT} = 0 \sim 3.6 \text{ V}$		V _{IN} , V _{OUT} = 0~3.6 V		V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μA
	rront	Icc	V _{IN} = V _{CC} or GND		1.8	_	20.0					
Quiescent supply cu	Quiescent supply current		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8		±20.0	μA				

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	ymbol Test Condition		Min	Мах	Unit
Unaracteristics	Cymbol		$V_{CC}(V)$	IVIIII	Max	Unit
	+		1.8	1.5	9.8	
Propagation delay time (D-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.1	ns
	t _{pHL}		$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.1	
			1.8	1.5	9.8	
Propagation delay time (LE-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.3	ns
	t _{pHL}		$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.5	ns
	^t pZH		3.3 ± 0.3	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.7	ns
3-state output disable time	t _{pLZ} t _{pHZ}		2.5 ± 0.2	0.8	4.3	
			3.3 ± 0.3	0.6	3.9	
		Figure 1, Figure 2	1.8	4.0	_	
Minimum pulse width (LE)	t _{w (H)}		2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0		
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			$\textbf{3.3}\pm\textbf{0.3}$	1.0	_	
			1.8	_	1.5	
Output to output skew	t _{osLH}	(Note)	2.5 ± 0.2	_	1.5	ns
	t _{osHL}		$\textbf{3.3}\pm\textbf{0.3}$	_	1.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0 \text{ ns}$, C_L = 30 pF)

Characteristics	Symbol	Test Condition	Test Condition		Тур.	
	e yzei			$V_{CC}\left(V\right)$.) p.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	1.8	0.15	
Quiet output maximum dynamic V_{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	0.35	
	V _{OLV}	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	-0.15	v
Quiet output minimum dynamic V_{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	2.5	-0.25	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	-0.35	
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	1.55	
Quiet output minimum dynamic V_{OH}	V _{OHV}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.65	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol Test Condition				Тур.	Unit
Characteristics	Symbol	Test Condition		V _{CC} (V)	тур.	Unit
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	C _{OUT}			1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (N	Note)	1.8, 2.5, 3.3	20	pF

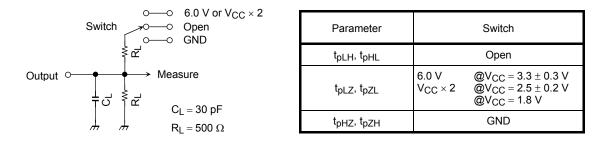
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

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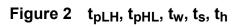
AC Test Circuit

AC Waveform





t_f 2.0 ns t_r 2.0 ns - V_M 90% Input VM (LE) Vм 10% GND t_{w (H)} t_r 2.0 ns t_f 2.0 ns 55 V_{M} 90% Input Vм Vм (D) 10% -55 - GND t_{h (L)} t_{s (H)} t_{h (H)} t_{s (L)} ς۶ · V_{OH} Output ́Vм (Q) ٧м - V_{OL} tpHL tpLH tpHL tpLH



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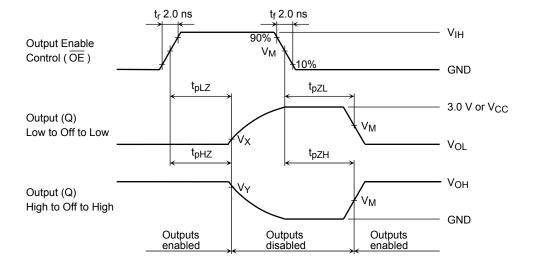


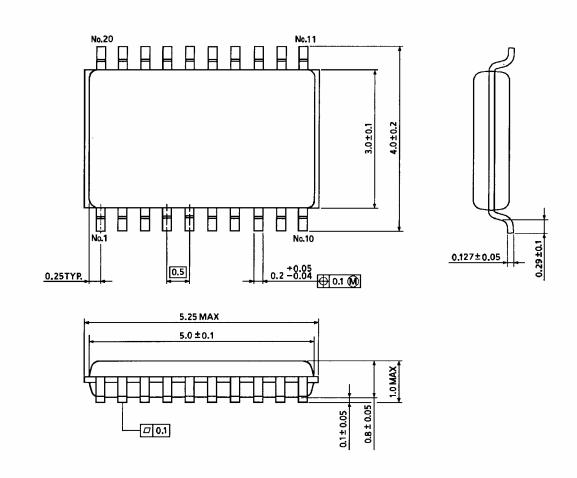
Figure 3 t _{pL}	z, t _{pHZ} ,	t _{pZL} , t	t _{pZH}
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Symbol	V _{CC}							
Symbol	$3.3\pm0.3\;V$	$2.5\pm0.2~\text{V}$	1.8 V					
VIH	2.7 V	V _{CC}	V _{CC}					
VM	1.5 V	V _{CC} /2	V _{CC} /2					
VX	V_{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V					
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V					

Package Dimensions

V\$\$OP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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